

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 (Currently Amended): An apparatus, comprising:

a semiconductor substrate; and

first and second support structures formed on the substrate, the second support structure at least partially surrounding the first support structure on the substrate,

the first and second support structures each **arranged beneath and** configured to support an electrical connector to be formed over the first and second support structures on the substrate.

2 (Original): The assembly of claim 1 wherein the first and second support structures each overlay electronic circuitry fabricated on a semiconductor die.

3 (Original): The assembly of claim 2 wherein the second support structure is electrically insulated from the first support structure, so as to reduce the capacitance generated between the second support structure and the electronic circuitry.

4 (Original): The assembly of claim 1 wherein the first support structure further comprises a substantially circular cross-section.

5 (Original): The assembly of claim 1 wherein the first support structure is made of aluminum.

6 (Original): The assembly of claim 1 wherein the second support structure further comprises a substantially annular cross-section located approximately concentric with the first support structure.

7 (Original): The assembly of claim 1 wherein the second support structure is made of aluminum.

8 (Original): The assembly of claim 1 wherein the semiconductor substrate has a geometric center, and wherein the first support structure further comprises a conductive element having at least a portion oriented toward said geometric center.

10/729,389
NSC1 P285/P05744

9 (Original): The assembly of claim 8 wherein the second support structure further comprises a substantially annular circumferential segment, the circumferential segment being located approximately concentric with the first support structure and electrically insulated from the conductive element.

10 (Original): An assembly for supporting an electrical connector with minimal parasitic capacitance, comprising:

first and second pads formed on a semiconductor substrate, the first and second pads underlying a solder bump interconnect and overlaying electronic circuitry;

the second pad at least partially surrounding the first pad so as to support the solder bump interconnect; and

the second pad being electrically insulated from the first pad so as to reduce the capacitance generated between the second pad and the electronic circuitry.

11 (Original): The assembly of claim 10 wherein the first and second pads each overlay electronic circuitry fabricated on a semiconductor die.

12 (Original): The assembly of claim 10 wherein the first pad further comprises a substantially circular cross-section.

13 (Original): The assembly of claim 10 wherein the first pad is made of aluminum.

14 (Original): The assembly of claim 10 wherein the second pad further comprises a substantially annular cross-section located approximately concentric with the first pad.

15 (Original): The assembly of claim 10 wherein the second pad is made of aluminum.

16 (Original): The assembly of claim 10 wherein the semiconductor substrate has a geometric center, and wherein the first pad further comprises a conductive element having at least a portion oriented toward said geometric center.

10/729,389
NSC1 P285/P05744

17 (Original): The assembly of claim 16 wherein the second pad further comprises a substantially annular circumferential segment, the circumferential segment being located approximately concentric with the first pad and electrically insulated from the conductive element.

Claims 18-25 (Cancelled).

26. (New): An apparatus, comprising:
a semiconductor substrate; and
first and second support structures formed on the substrate, the second support structure at least partially surrounding the first support structure on the substrate,
the first and second support structures each configured to support an electrical connector to be formed over the first and second support structures on the substrate,
the second support structure comprising a substantially annular cross-section located approximately concentric with the first support structure.

10/729,389
NSC1 P285/P05744